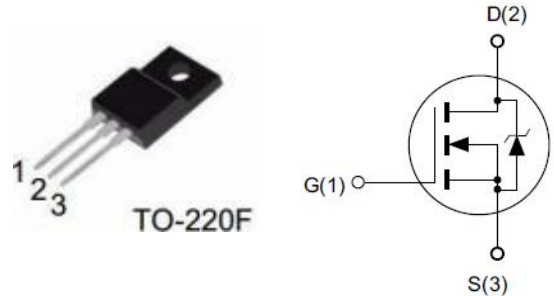


Features

- ◆ 650V, 4A, $R_{DS(ON)}(Typ.) = 2.40\Omega @ V_{GS} = 10V$.
- ◆ Low C_{rss}
- ◆ Fast Switching
- ◆ 100% Avalanche Tested

Application

- ◆ Adaptor
- ◆ Standby Power
- ◆ Switching power supply
- ◆ LED Power



Absolute Maximum Ratings $T_c = 25^\circ \text{C}$ unless otherwise noted

Symbol	Parameter	Rating	Unit
V_{DS}	Drain-Source Voltage ^a	650	V
V_{GS}	Gate-Source Voltage	± 30	V
I_D	Drain Current-Continuous, $T_c = 25^\circ \text{C}$	4	A
	Drain Current-Continuous, $T_c = 100^\circ \text{C}$	2.4	A
I_{DM}	Drain Current-Pulsed ^b	16	A
P_D	Maximum Power Dissipation @ $T_J = 25^\circ \text{C}$	30	W
E_{AS}	Single Pulsed Avalanche Energy ^c	125	mJ
T_J, T_{STG}	Operating and Store Temperature Range	150, -55 to 150	$^\circ \text{C}$

Thermal Characteristics

Symbol	Parameter	Value	Unit
$R_{\theta JC}$	Thermal Resistance, Junction to Case	4.15	$^\circ \text{C/W}$
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	62.5	$^\circ \text{C/W}$

Electrical Characteristics $T_J = 25^\circ \text{C}$ unless otherwise noted

■ Off Characteristics

Symbol	Parameter	Test Condition	Min.	Typ.	Max.	Unit
BV_{DSS}	Drain-Source Breakdown Voltage	$V_{GS} = 0V, I_D = 250\mu A$	650	-	-	V
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS} = 650V, V_{GS} = 0V$	-	-	1	μA
I_{GSS}	Forward Gate Body Leakage Current	$V_{DS} = 0V, V_{GS} = \pm 30V$	-	-	± 100	nA



MPF04N65B

N-Channel Power MOSFET

■ On Characteristics

Symbol	Parameter	Test Condition	Min.	Typ.	Max.	Unit
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_D = 250\mu A$	2.0	-	4.0	V
$R_{DS(on)}$	Static Drain-Source On-Resistance	$V_{GS} = 10V, I_D = 2A$	-	2.40	2.80	Ω

■ Dynamic Characteristics

Symbol	Parameter	Test Condition	Min.	Typ.	Max.	Unit
R_G	Gate Resistance	$f = 1.0MHz$ open drain	-	3	-	Ω
C_{iss}	Input Capacitance	$V_{DS} = 25V,$ $V_{GS} = 0V,$ $f = 1.0MHz$	-	580	-	pF
C_{oss}	Output Capacitance		-	51	-	pF
C_{rss}	Reverse Transfer Capacitance		-	4.9	-	pF

■ On Characteristics

Symbol	Parameter	Test Condition	Min.	Typ.	Max.	Unit
$t_{d(on)}$	Turn-On Delay Time	$V_{DD} = 320V,$ $I_D = 4A,$ $V_{GS} = 10V,$ $R_{GEN} = 24\Omega$	-	14	-	ns
t_r	Turn-On Rise Time		-	16	-	ns
$t_{d(off)}$	Turn-Off Delay Time		-	32	-	ns
t_f	Turn-Off Fall Time		-	11	-	ns
Q_g	Total Gate Charge	$V_{DS} = 520V,$ $I_D = 4A,$ $V_{GS} = 10V$	-	14.8	-	nC
Q_{gs}	Gate-Source Charge		-	4.2	-	nC
Q_{gd}	Gate-Drain Charge		-	5.0	-	nC

■ Drain-Source Diode Characteristics

Symbol	Parameter	Test Condition	Min.	Typ.	Max.	Unit
I_S	Drain-Source Diode Forward Continuous Current	$V_{GS} = 0V$	-	-	4	A
I_{SM}	Maximum Pulsed Current	$V_{GS} = 0V$	-	-	16	A
V_{SD}	Drain-Source Diode Forward Voltage	$V_{GS} = 0V, I_S = 4A$	-	-	1.2	V
T_{rr}	Body Diode Reverse Recovery Time	$I_S = 4A, V_{GS} = 0V$ $di_F/dt = 100A/\mu s$	-	256	-	ns
Q_{rr}	Body Diode Reverse Recovery Charge		-	1.2	-	μC

Notes:

- $T_J = +25^\circ C$ to $+150^\circ C$
- Repetitive rating; pulse width limited by maximum junction temperature.
- $L = 10mH, V_{DD} = 50V, I_{AS} = 5A, R_G = 25\Omega$ Starting $T_J = 25^\circ C$.

■ Characteristic Curve

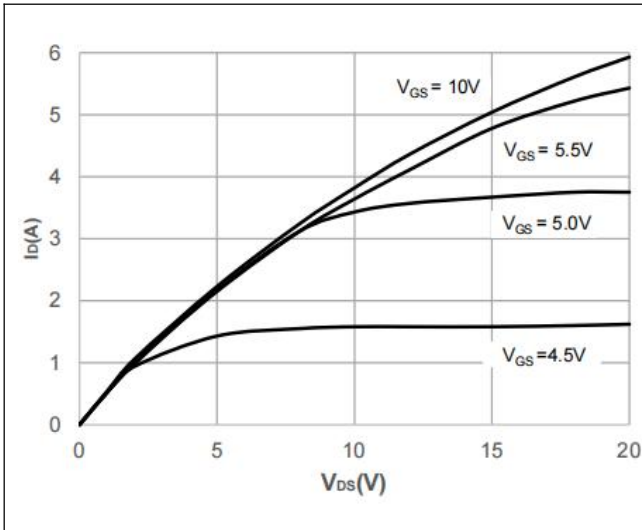


Figure 1. Typical Output Characteristics

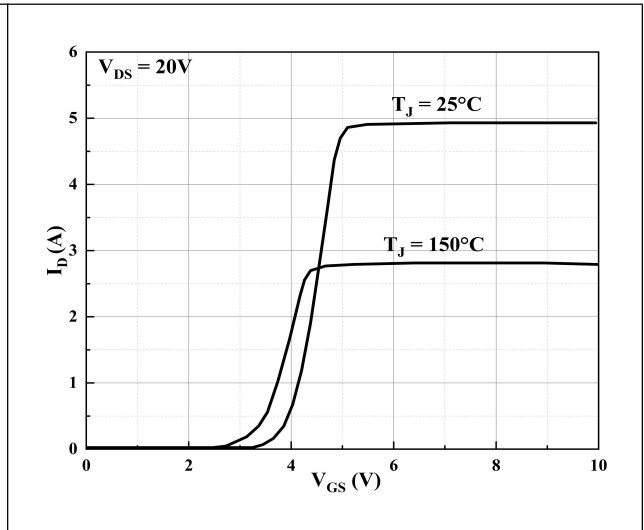


Figure 2. Typical Transfer Characteristics

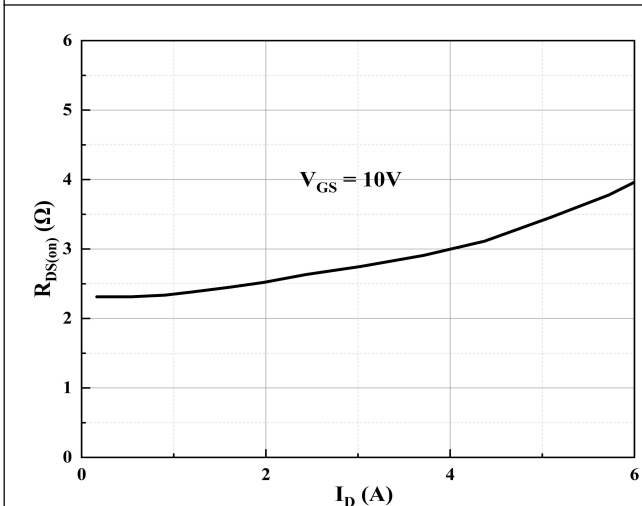


Figure 3. On- Resistance vs. Drain Current

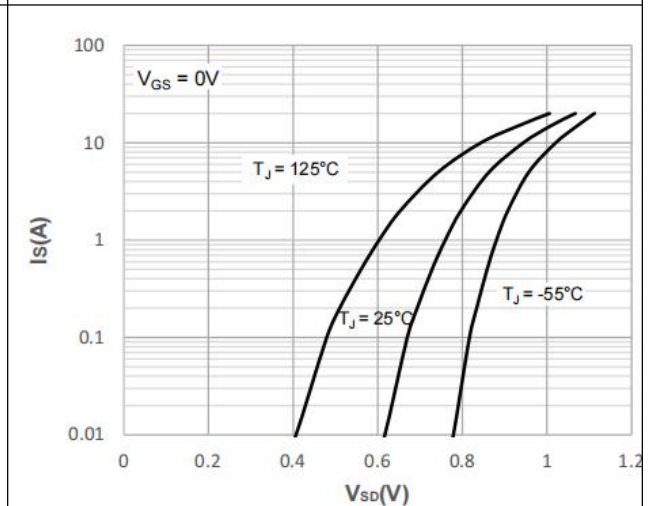


Figure 4. Body-Diode Characteristics

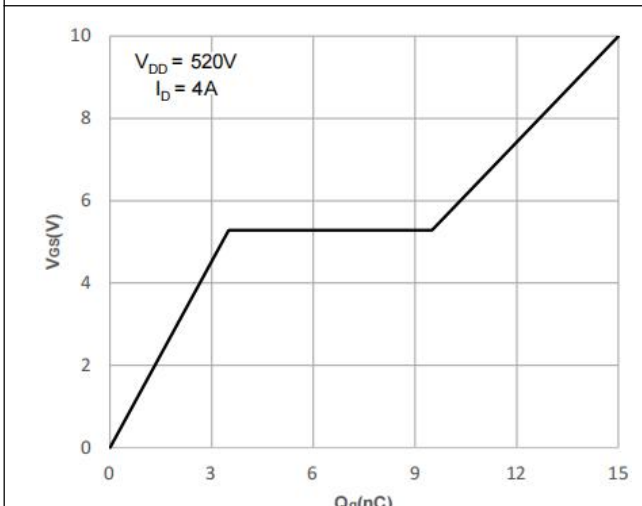


Figure 5. Gate-Charge Characteristics

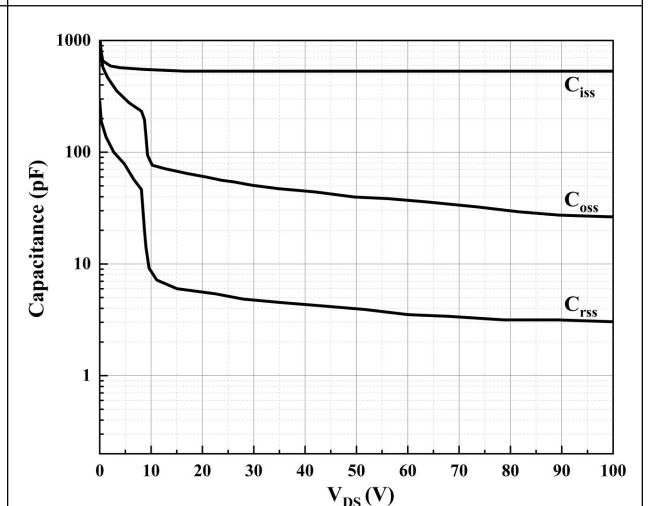


Figure 6. Capacitance Characteristics

■ Characteristic Curve

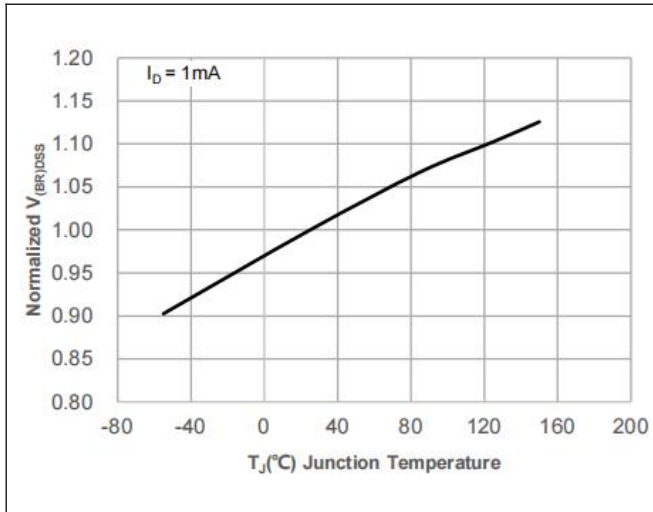


Figure 7. Normalized Breakdown voltage vs. Junction Temperature

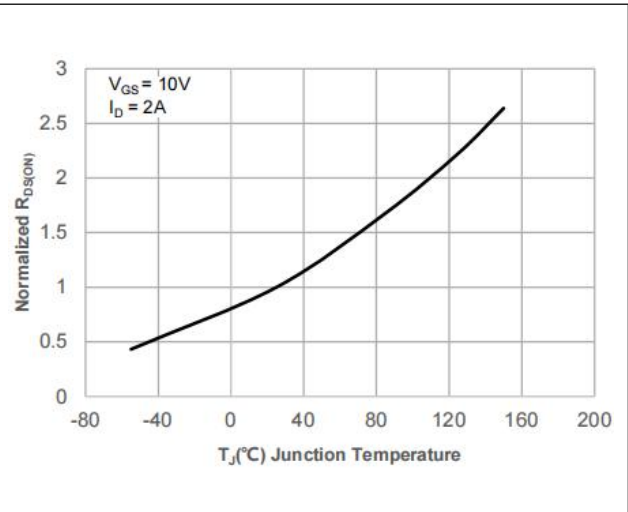


Figure 8. Normalized on Resistance vs. Junction Temperature

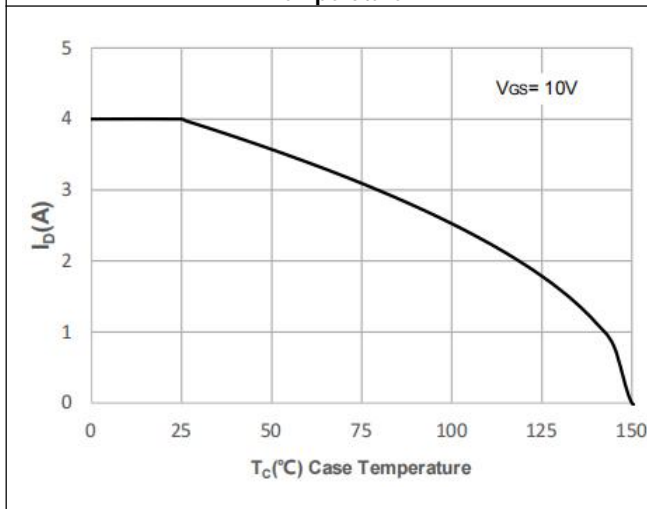


Figure 9: Maximum Continuous Drain Current vs. Case Temperature

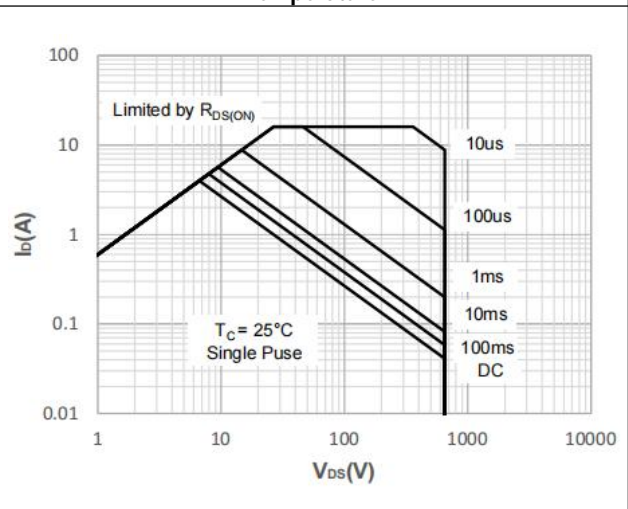


Figure 10: Maximum Safe Operating Area

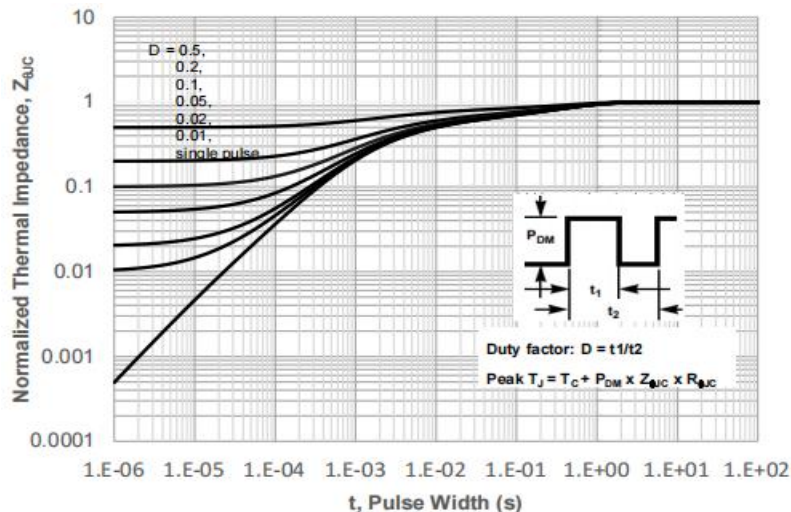


Figure 11: Normalized Maximum Transient Thermal Impedance

■ Package Information

